EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S23	2689	(438/222,478,479,481).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/01 13:54
S24	5238	(epi or epitaxial or epitaxially) near8 (reactor or chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 13:56
S25	8595965	((inert or carrier) near gas) or Helium or He or Nitrogen or N or "N.sub.2"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 13:57
S26	189077	phosphine or phosphorous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 13:59
S27	4879	silane same dichlorosilane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:00
S28	12	S24 same S25 same S26 same S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:00
S29	572907	(form or formed or forming or deposit or depositing or deposited or provide or provided or providing) near8 (Si or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:03
S30	11	S28 and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:03
S31	47	("4714594").PN. OR ("4846102").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/01 14:07
S32	6	S31 and S26 and S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:50

S33	5242	(epi or epitaxial or epitaxially) near8 (reactor or chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S34	8598224	((inert or carrier) near gas) or Helium or He or Nitrogen or N or "N.sub.2"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S35	189184	phosphine or phosphorous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S36	4887	silane same dichlorosilane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S37	12	S33 same S34 same S35 same S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S38	573286	(form or formed or forming or deposit or depositing or deposited or provide or provided or providing) near8 (Si or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S39	11	S37 and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S40	3926	(438/142,197,299,300).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/03 13:52
S41	11	S39 and (S/D or source/drain or source or drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:53
S42	11	S41 and (phosphine or phosphorous or P or "PH.sub.3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 14:48
S43	1778593	(MOS or MOSFET or transistor or FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 14:57

S44	6988	(switch$4 or change or changed or changing or alternat$4 or replace or replaced or replacing) near8 ((inert or Nitrogen or "N.sub.2") near8 (hydrogen or "H.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 15:13
S45	148	(S33 and S34 and S35 and S36)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 15:13
S46	806	(438/300).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/03 15:14
S47	13	S45 and S46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 15:14
S48	2	("6251188").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/03 16:27
S49	8	("20030003646" | "5378651" | "6251188" | "6391749").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 19:11
S50	5242	(epi or epitaxial or epitaxially) near8 (reactor or chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09
S51	8598224	((inert or carrier) near gas) or Helium or He or Nitrogen or N or "N.sub.2"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09
S52	189184	phosphine or phosphorous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09
S53	4887	silane same dichlorosilane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09
S54	148	(S50 and S51 and S52 and S53)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09

S55	37261	(raise or raised or elevate or elevated or elevating) near8 (source or drain or S/D or source/drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:11
S56	41	S54 and S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:11
S57	14	S56 and (((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:11
S58	237	(Raised near4 (source/drain)) same MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:15
S59	2	S58 and (silane or "SiH.sub.4") and (dichlorosilane or DCS) and (phosphine or phosphorous or "PH.sub.3") and (nitrogen or "N.sub.2" or hydrogen or "H.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:17
S60	103	("20010001724" | "20010009303" | "20010031535" | "20010045604" | "20020019127" | "20020048910" | "20020052084" | "20020056879" | "20020063292" | "20020190284" | "20030113971" | "20040007724" | "20040014276" | "20040014304" | "20040070035" | "20040084735" | "20040119101" | "20040142545" | "20040173815" | "4717681" | "4755478" | "4803539" | "5034348" | "5089872" | "5198689" | "5217923" | "5242847" | "5334861" | "5336903" | "5346840" | "5442205" | "5496750" | "5496771" | "5659194" | "5714777" | "5844260" | "5847419" | "5869359" | "5877535" | "5891769" | "5933741" | "5998807" | "6008111" | "6066563" | "6096647" | "6107653" | "6121100" | "6132806" | "6133124" | "6159856" | "6187657" | "6214679" | "6235575" | "6246077" | "6251780" | "6268257" | "6281532" | "6291321" | "6294448" | "6306698" | "6313486" | "6315384" | "6316357" | "6319805" | "6362071" | "6380008" | "6399970" | "6406986" |	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/04 09:20

		"6410371" | "6461960" | "6486520" | "6498359" | "6503833" | "6509587" | "6555839" | "6555880" | "6562703" | "6563152" | "6566718" | "6573126" | "6573160" | "6583015" | "6593191" | "6593641" | "6603156" | "6605498" | "6621131" | "6657223" | "6682965" | "6686617" | "6699765" | "6703648" | "6724019" | "6743684").PN. OR ("6946371").URPN.				
S61	10	S60 and (silane or "SiH.sub.4") and (dichlorosilane or DCS) and (phosphine or phosphorous or "PH.sub.3") and (nitrogen or "N.sub.2" or hydrogen or "H.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:22
S62	0	(epitaxial near4 reactor4 near chamber) same (mixture near8 (chlorosilane or dichlorosilane or trichlorosilane or tetrachlorosilane or DCS) near8 (silane or "SiH.sub.4"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:32
S64	1	(epitaxial near4 reactor near4 chamber) same (mixture near8 (chlorosilane or dichlorosilane or trichlorosilane or tetrachlorosilane or DCS) near8 (silane or "SiH.sub.4"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:33
S65	2	("6184154").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/14 10:49
S66	206100	(Silane or "SiH.sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:15
S67	986025	dichlorosilane or dichloro-silane or DCS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:16
S68	195485	phosphorous or phosphine or "PH.sub.3"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:17
S69	181769	(inert or purge or purged) near8 (nitrogen or "N.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:17

S70	1171	S66 and S67 and S68 and S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:17
S71	21	S66 same S67 same S68 same S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:18
S72	5117937	(silicon or Si or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:20
S73	21	S71 and S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:20
S74	11	S73 and (((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:21
S75	1411	n-type near8 silicon near8 (phosphine or phosphorous or "PH.sub.3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:24
S76	10	S75 and (epitaxial near reactor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:27
S77	2	("6184154").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/14 13:49
S78	8	("20030003646" | "5378651" | "6251188" | "6391749").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:01
S79	2	S78 and MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:47
S80	6646	S66 same S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:48

S81	42	S80 and MOSFET and (elevated near4 source/drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:49
S82	10	S81 and ((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:50
S83	1	S82 and (bipolar near transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:52
S84	51	S80 and (bipolar near transistor) and (base near region) and (emitter near region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:53
S85	49	S84 and ((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:53
S86	29	S85 and (epitaxial near4 (grow or growing or growth))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:54
S87	14	S86 and pnp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:55
S88	469	(epitaxial$4 near8 (grow or growed or growing or growth)) near8 (base near8 emitter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:58
S89	5	S85 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:59
S90	5	S89 and n-type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:59
S91	1610	Alonso.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 15:26

S92	2	S91 and (epitaxial near8 growth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 15:27
S93	2	S91 and (epitaxial near8 growth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 15:28
S94	2	(phosphorous near8 n-type) near8 (epitaxial near8 source/drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/15 09:10
S106	40	(epitaxial near reactor) near8 LPCVD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/16 16:59
S107	12	MOSFET and (raised near8 source/drain) and (epitaxial near reactor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/16 17:02
S108	5	S107 and ((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/16 17:04
S109	3	MOSFET and ((epitaxial near8 (raised near4 source/drain)) same reactor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/16 17:30

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